

## ABSTRACT

A method of making an electrically operated memory element.  
The memory element having a contact in electrical communication  
5 with a memory material programmable to at least a first resistance  
state and a second resistance state. Preferably, the contact  
includes at least a first region having a first resistivity and a  
second region having a second resistivity greater than the first  
resistivity where the more resistive region is adjacent to the  
10 memory material.